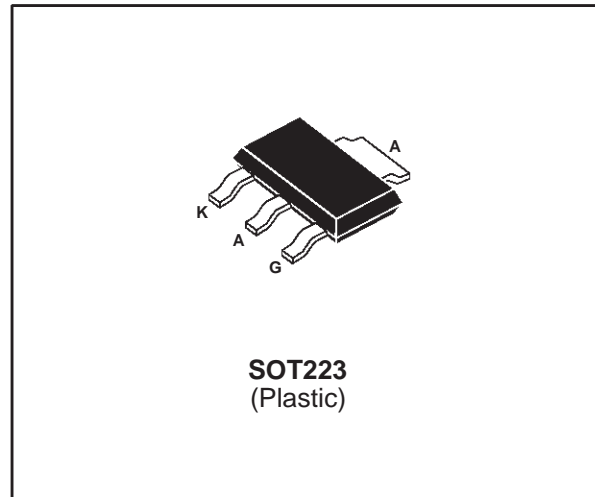


SENSITIVE SCR
FEATURES

- $I_{T(RMS)} = 0.8A$
- $V_{DRM} / V_{RRM} = 200V$ to $600V$

DESCRIPTION

High performance planar technology. These parts are intended for general purpose applications where low gate sensitivity is required.


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$ *	RMS on-state current (180° conduction angle)	$T_a = 70^\circ C$	0.8	A
$I_{T(AV)}$ *	Mean on-state current (180° conduction angle)	$T_a = 70^\circ C$	0.5	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	8	A
		$t_p = 10$ ms	7	
I^2t	I^2t Value for fusing	$t_p = 10$ ms	0.24	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 10$ mA $di_G/dt = 0.1$ A/ μs .		30	A/ μs
T_{stg} T_j	Storage temperature range Operating junction temperature range		- 40, + 150 - 40, + 125	$^\circ C$
TI	Maximum lead temperature for soldering during 10s		260	$^\circ C$

* : With $5cm^2$ copper ($e=35\mu m$) surface under tab.

Symbol	Parameter	Voltage			Unit
		B	D	M	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$ $R_{GK} = 1K$	200	400	600	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient *	60	°C/W
Rth(j-l)	Junction to tab for DC	30	°C/W

* : With 5cm² copper (e=35µm) surface under tab.

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 0.1\text{ W}$ $P_{GM} = 2\text{ W}$ ($t_p = 20\ \mu\text{s}$) $I_{GM} = 1\text{ A}$ ($t_p = 20\ \mu\text{s}$)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Sensitivity			Unit
				09	02	11	
I _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MIN	-	-	4	µA
			MAX	1	200	25	
V _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MAX	0.8			V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ R _{GK} = 1 KΩ	T _j = 125°C	MIN	0.1			V
V _{GRM}	I _{RG} =10µA	T _j = 25°C	MIN	8			V
tgd	V _D =V _{DRM} I _{TM} = 3 x I _{T(AV)} dI _G /dt = 0.1A/µs I _G = 10mA	T _j = 25°C	TYP	0.5			µs
I _H	I _T = 50mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	5			mA
I _L	I _G =1mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	6			mA
V _{TM}	I _{TM} = 1.6A t _p = 380µs	T _j = 25°C	MAX	1.95			V
I _{DRM} I _{RRM}	V _D = V _{DRM} R _{GK} = 1 KΩ V _R = V _{RRM}	T _j = 25°C	MAX	B/D: 1 - M: 10			µA
		T _j = 125°C	MAX	100			µA
dV/dt	V _D = 67%V _{DRM} R _{GK} = 1 KΩ	T _j = 125°C	MIN	50	75	80	V/µs
tq	I _{TM} = 3 x I _{T(AV)} V _R =35V dI/dt=10A/µs t _p =100µs dV/dt=10V/µs V _D = 67%V _{DRM} R _{GK} = 1 KΩ	T _j = 125°C	MAX	200			µs

Fig.1 : Maximum average power dissipation versus average on-state current.

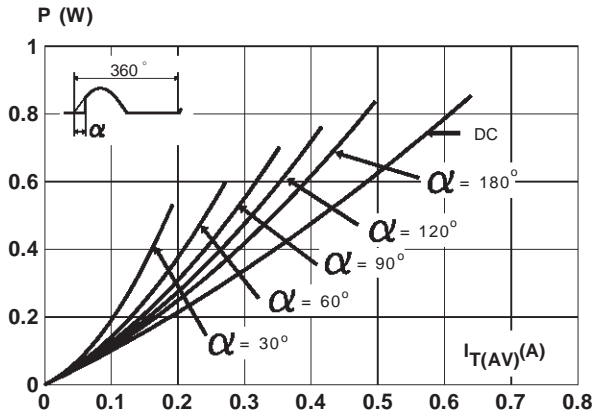


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Ttab).

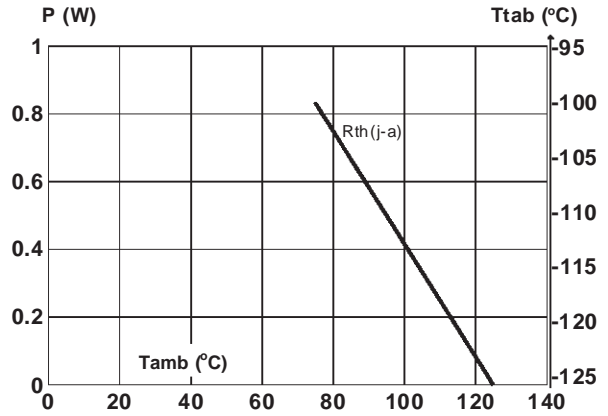


Fig.3 : Average on-state current versus tab temperature.

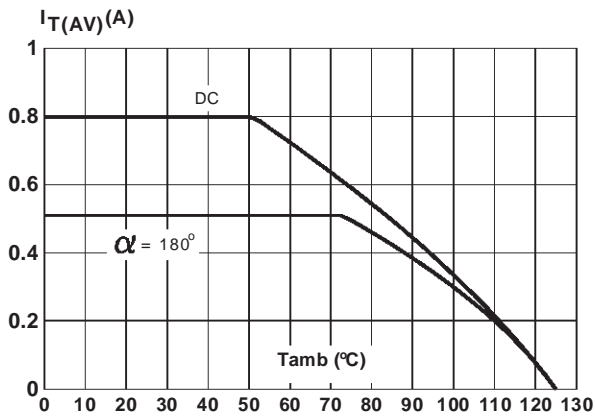


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

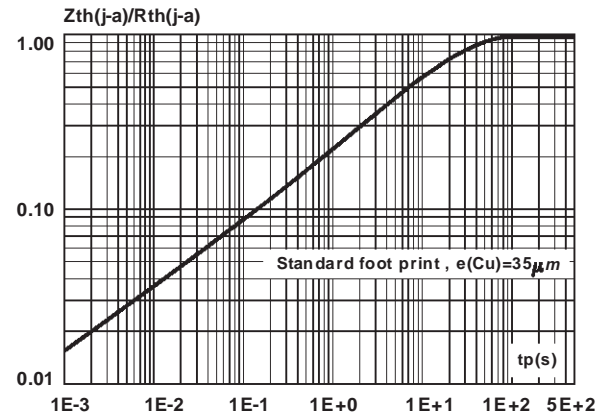


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

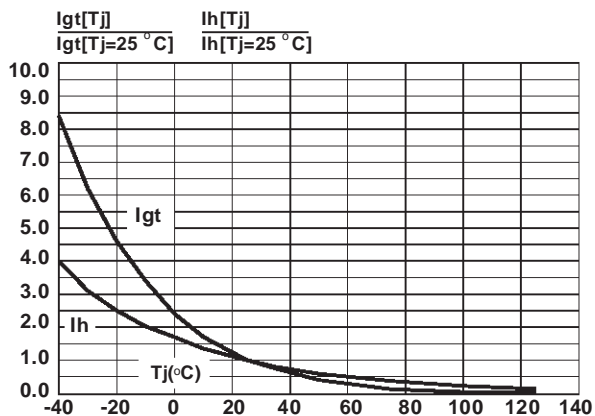


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

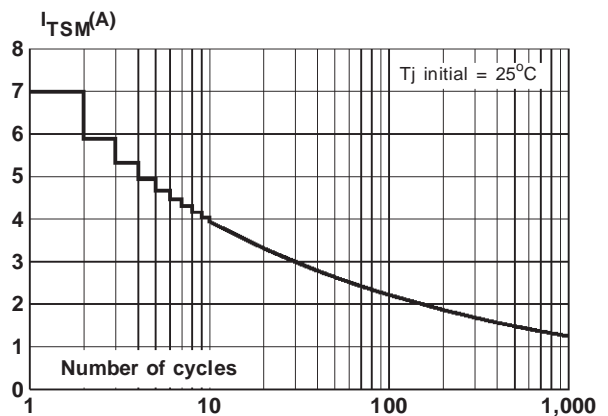


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p @ 10ms$, and corresponding value of I^2t .

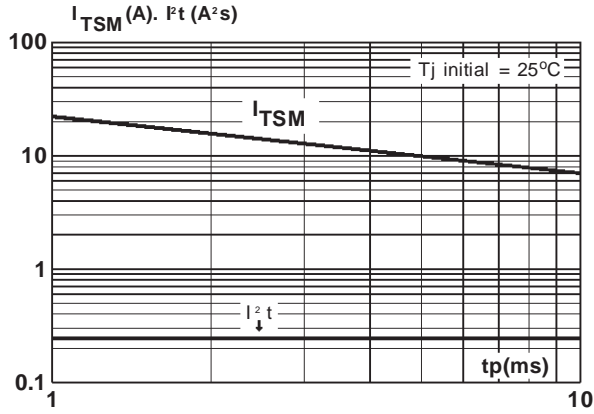


Fig.8 : On-state characteristics (maximum values).

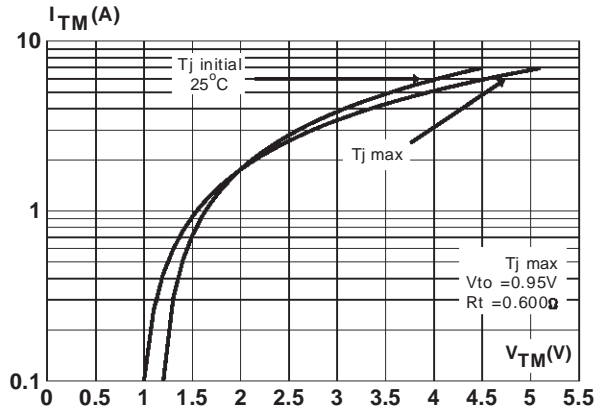
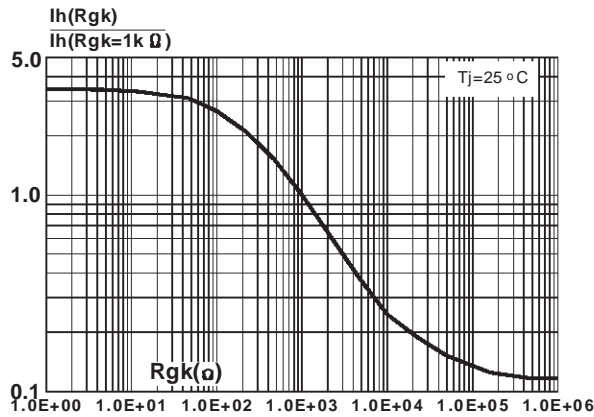
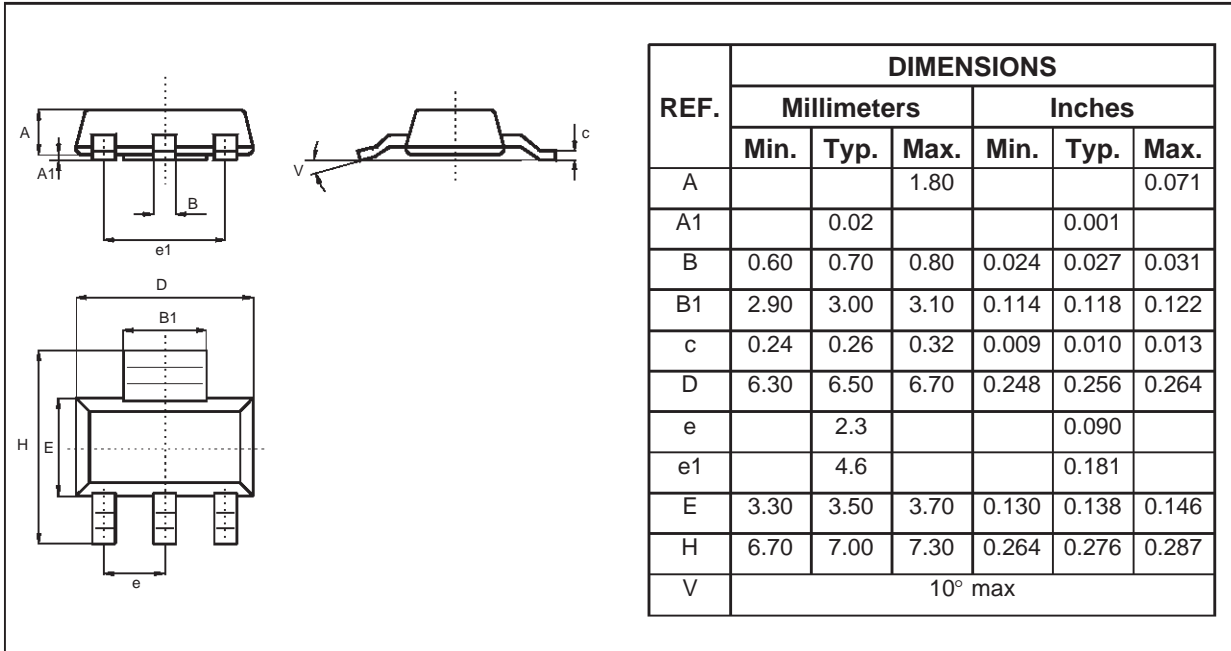


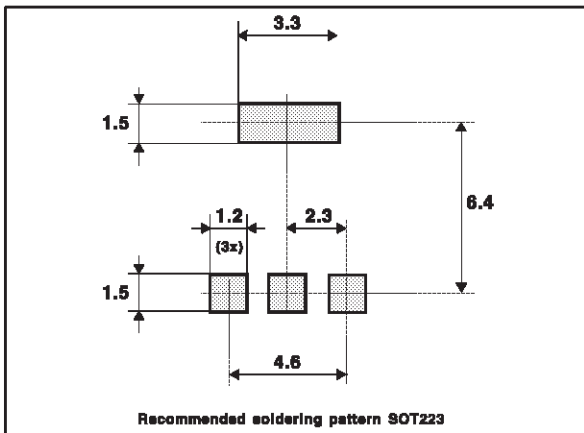
Fig.9 : Relative variation of holding current versus gate-cathode resistance (typical values).



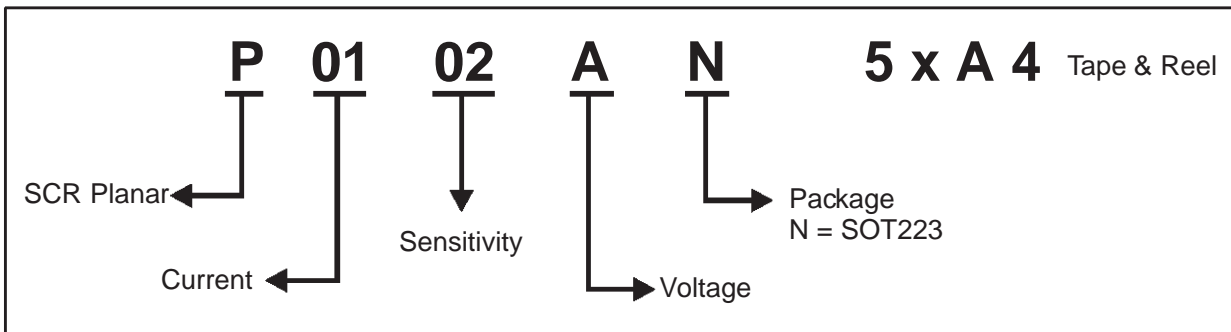
PACKAGE MECHANICAL DATA
SOT223 (Plastic)



FOOT PRINT



ORDERING INFORMATION



P01xxxN

MARKING

Type	Marking	Package	Weight	Delivery mode	Base qty
P0102BN	P2B	SOT223	0.11g	Tape & Reel	1000
P0109BN	P9B				
P0111BN	P1B				
P0102DN	P2D				
P0109DN	P9D				
P0111DN	P1D				
P0102MN	P2M				
P0109MN	P9M				
P0111MN	P1M				

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